July 2014



Features

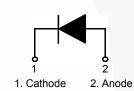
- + High Speed Switching ($\rm t_{rr}=45ns(Typ.) @ I_F=50A$)
- Low Forward Voltage(V_F=1.67V(Typ.) @ I_F=50A)
- Avalanche Energy Rated
- AEC-Q101 Qualified

Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose
- Automotive and General Purpose

Pin Assignments





Max Ratings (600V, 50A)

power loss in the switching transistors.

The RHRG5060_F085 is an Hyperfast[™] diode with soft recovery characteristics (trr < 45ns). It has half the

recovery time of ultrafast diode and is of silicon nitride

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of automotive switch-

ing power supplies and other power switching automotive applications. Its low stored charge and

hyperfast soft recovery minimize ringing and electrical

noise in many power switching circuits, thus reducing

passivated ion-implanted epitaxial planar construction.

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{RRM}	Peak Repetitive Reverse Voltage	600	V	
V _{RWM}	Working Peak Reverse Voltage	600	V	
V _R	DC Blocking Voltage	600	V	
I _{F(AV)}	Average Rectified Forward Current@ $T_C = 25^{\circ}C$	50	А	
I _{FSM}	Non-repetitive Peak Surge Current (Halfwave 1 Phase 50Hz)	150	A	
E _{AVL}	Avalanche Energy (1.4A, 40mH)	40	mJ	
T _{J,} T _{STG}	Operating Junction and Storage Temperature	- 55 to +175	°C	

Thermal Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Мах	Units
$R_{ ext{ heta}JC}$	Maximum Thermal Resistance, Junction to Case	0.42	°C/W
$R_{ ext{ heta}JA}$	Maximum Thermal Resistance, Junction to Ambient	45	°C/W

Package Marking and Ordering Information

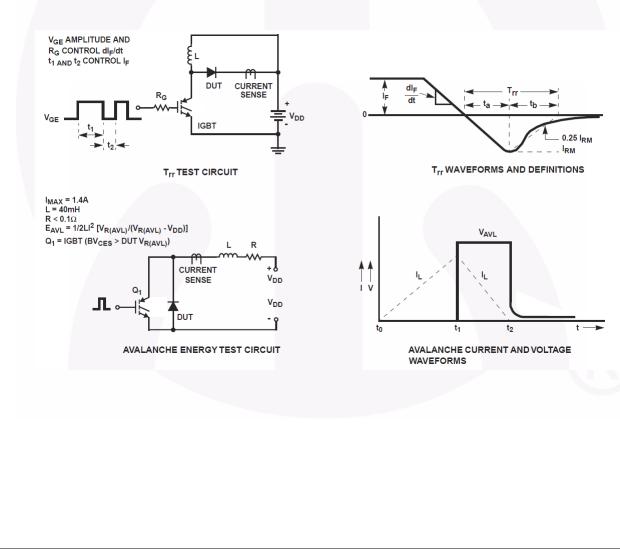
Device Marking	Device	Package	Tube	Quantity
RHRG5060	RHRG5060_F085	TO-247	-	30

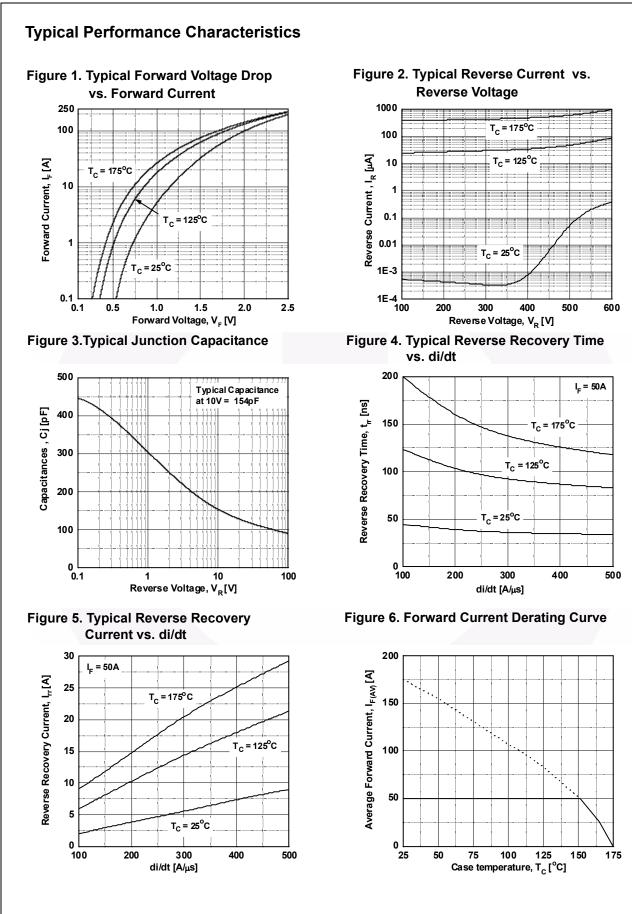
Symbol	Parameter Instantaneous Reverse Current	Conditions		Min.	Тур.	Max	Units
		V _R = 600V	T _C = 25 °C	-	-	250	uA
			T _C = 175 °C	-	-	1.5	mA
V _{FM} ¹	Instantaneous Forward Voltage	I _F = 50A	T _C = 25 °C T _C = 175 °C	-	1.67 1.29	2.1 1.7	V V
t _{rr} ² Reverse Recovery Time	Reverse Recovery Time	I _F =1A, di/dt = 100A/μs, V _{CC} = 390V	T _C = 25 °C	-	37	45	ns
		I_F =50A, di/dt = 100A/µs, V _{CC} = 390V	T _C = 25 °C T _C = 175 °C	-	45 200	60 -	ns ns
t _a t _b Q _{rr}	Reverse Recovery Time Reverse Recovery Charge	I _F =50A, di/dt = 100A/μs, V _{CC} = 390V	T _C = 25 °C	- - -	25 20 45	- - -	ns ns nC

Notes:

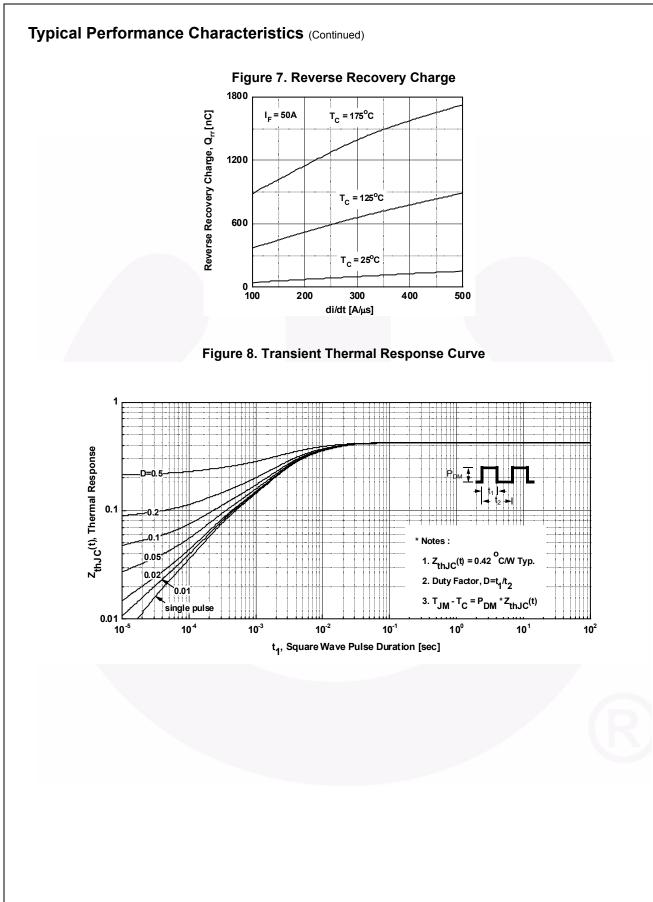
- 1. Pulse : Test Pulse width = $300\mu s$, Duty Cycle = 2%
- 2. Guaranteed by design

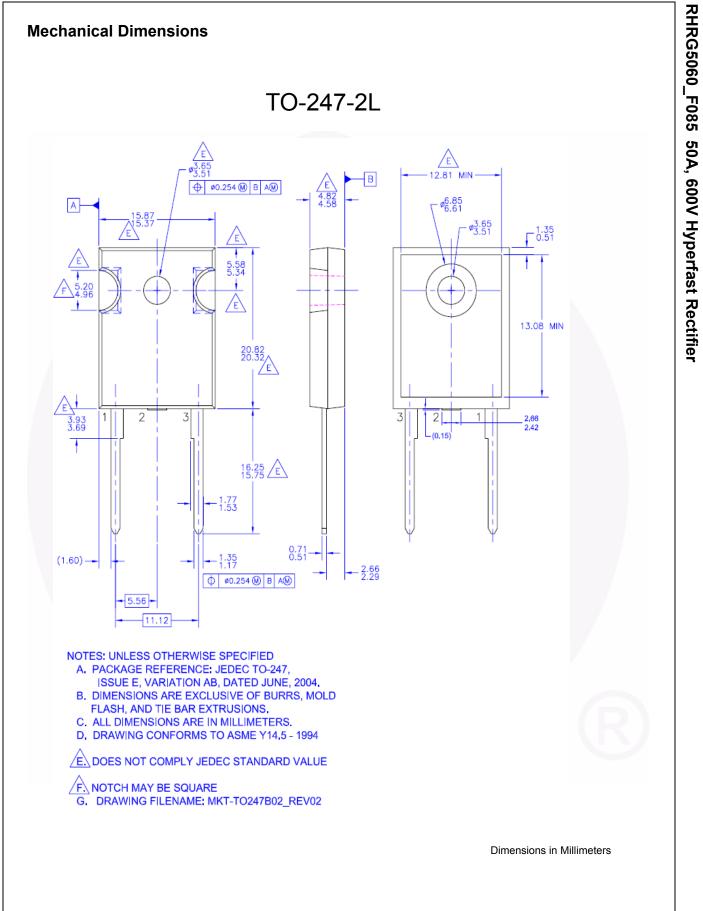
Test Circuit and Waveforms













Obsolete

Not In Production

Rev. 168

Datasheet contains specifications on a product that is discontinued by Fairchild

Semiconductor. The datasheet is for reference information only.